

NXS0102

Dual supply translating transceiver; open drain; auto direction sensing

Rev. 01 — 2 June 2010

Product data sheet

1. General description

The NXS0102 is a 2-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features two data input-output ports (An and Bn), one output enable input (OE) and two supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). $V_{CC(A)}$ can be supplied at any voltage between 1.65 V and 3.6 V and $V_{CC(B)}$ can be supplied at any voltage between 2.3 V and 5.5 V, making the device suitable for translating between any of the voltage nodes (1.8 V, 2.5 V, 3.3 V and 5.0 V). Pins An and OE are referenced to $V_{CC(A)}$ and pins Bn are referenced to $V_{CC(B)}$. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range:
 - ◆ $V_{CC(A)}$: 1.65 V to 3.6 V and $V_{CC(B)}$: 2.3 V to 5.5 V
- Maximum data rates:
 - ◆ Push-pull: 50 Mbps
- I_{OFF} circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - ◆ HBM JESD22-A114E Class 2 exceeds 2500 V for A port
 - ◆ HBM JESD22-A114E Class 3B exceeds 8000 V for B port
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1500 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Applications

- I²C/SMBus
- UART
- GPIO



4. Ordering information

Table 1. Ordering information

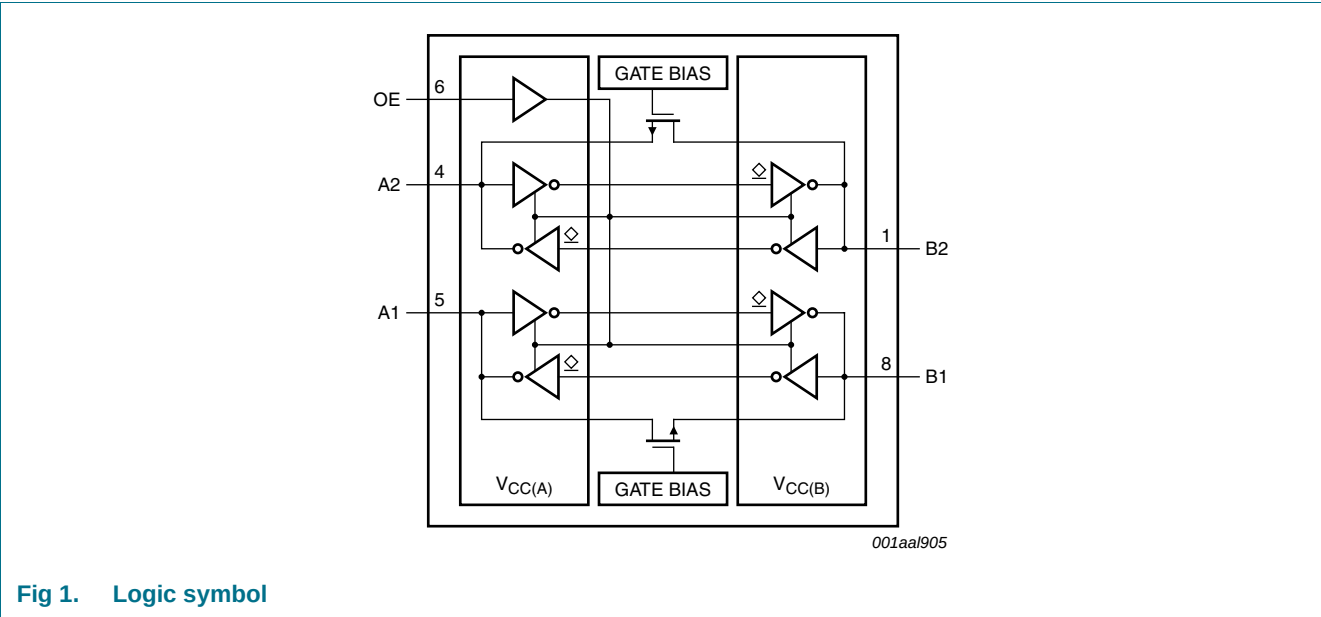
Type number	Package			
	Temperature range	Name	Description	Version
NXS0102DP	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
NXS0102GT	−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
NXS0102GD	−40 °C to +125 °C	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body 3 × 2 × 0.5 mm	SOT996-2
NXS0102GF	−40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089

5. Marking

Table 2. Marking

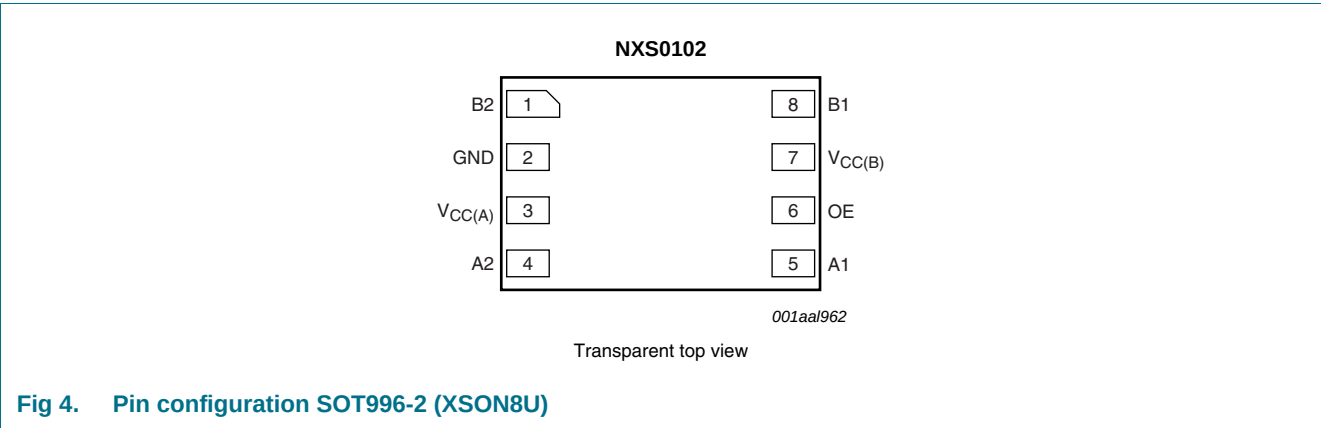
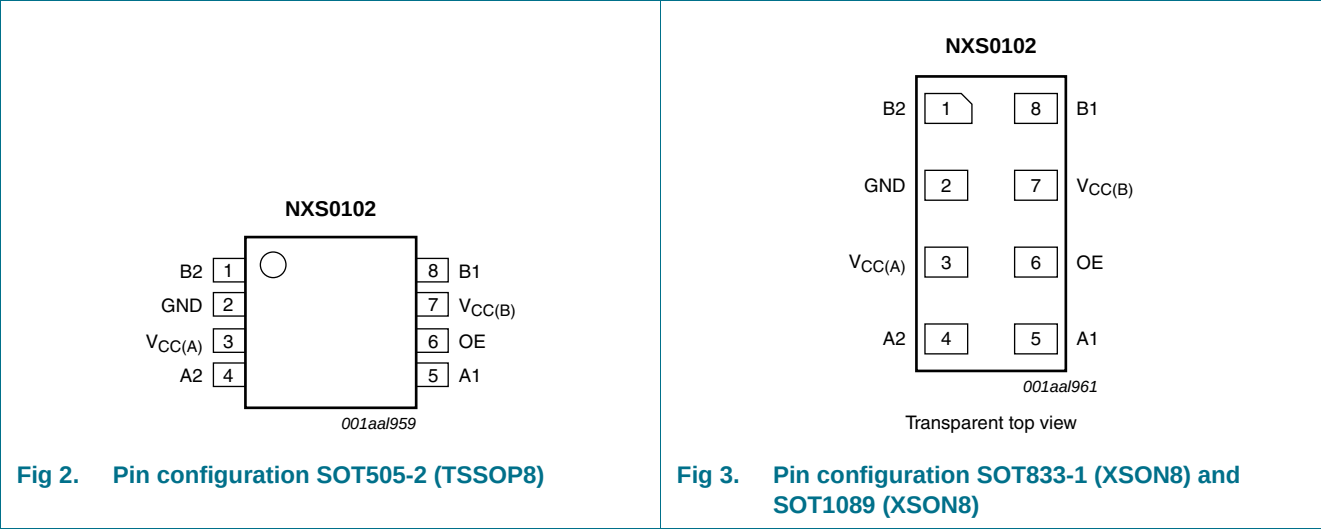
Type number	Marking code
NXS0102DP	s02
NXS0102GT	s02
NXS0102GD	s02
NXS0102GF	s2

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Symbol	Pin	Description
B2, B1	1, 8	data input or output (referenced to V _{CC(B)})
GND	2	ground (0 V)
V _{CC(A)}	3	supply voltage A
A2, A1	4, 5	data input or output (referenced to V _{CC(A)})
OE	6	output enable input (active HIGH; referenced to V _{CC(A)})
V _{CC(B)}	7	supply voltage B

8. Functional description

Table 4. Function table^[1]

Supply voltage		Input	Input/output	
V _{CC(A)}	V _{CC(B)}	OE	An	Bn
1.65 V to V _{CC(B)}	2.3 V to 5.5 V	L	Z	Z
1.65 V to V _{CC(B)}	2.3 V to 5.5 V	H	input or output	output or input
GND ^[2]	GND ^[2]	X	Z	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either V_{CC(A)} or V_{CC(B)} is at GND level, the device goes into power-down mode.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+6.5	V
V _{CC(B)}	supply voltage B		-0.5	+6.5	V
V _I	input voltage	A port and OE input	^{[1][2]} -0.5	+6.5	V
		B port	^{[1][2]} -0.5	+6.5	V
V _O	output voltage	Active mode	^{[1][2]}		
		A or B port	-0.5	V _{CCO} + 0.5	V
		Power-down or 3-state mode	^[1]		
		A port	-0.5	+4.6	V
		B port	-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
I _O	output current	V _O = 0 V to V _{CCO}	^[2] -	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] -	250	mW

[1] The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with the output.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For XSON8, XSON8U and XQFN8U packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions^{[1][2]}

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		1.65	3.6	V
$V_{CC(B)}$	supply voltage B		2.3	5.5	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	A or B port; push-pull driving			
		$V_{CC(A)} = 1.65\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 2.3\text{ V to }5.5\text{ V}$	-	10	ns/V
		OE input			
		$V_{CC(A)} = 1.65\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 2.3\text{ V to }5.5\text{ V}$	-	10	ns/V

[1] The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND.

[2] $V_{CC(A)}$ must be less than or equal to $V_{CC(B)}$.

11. Static characteristics

Table 7. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $T_{amb} = 25\text{ °C}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	input leakage current	OE input; $V_I = 0\text{ V to }3.6\text{ V}; V_{CC(A)} = 1.65\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 2.3\text{ V to }5.5\text{ V}$	-	-	± 1	μA
I_{OZ}	OFF-state output current	A or B port; $V_O = 0\text{ V or }V_{CCO}; V_{CC(A)} = 1.65\text{ V to }3.6\text{ V};$ $V_{CC(B)} = 2.3\text{ V to }5.5\text{ V}$	^[1] -	-	± 1	μA
I_{OFF}	power-off leakage current	A port; V_I or $V_O = 0\text{ V to }3.6\text{ V};$ $V_{CC(A)} = 0\text{ V}; V_{CC(B)} = 0\text{ V to }5.5\text{ V}$	-	-	± 1	μA
		B port; V_I or $V_O = 0\text{ V to }5.5\text{ V};$ $V_{CC(B)} = 0\text{ V}; V_{CC(A)} = 0\text{ V to }3.6\text{ V}$	-	-	± 1	μA
C_I	input capacitance	OE input; $V_{CC(A)} = 3.3\text{ V}; V_{CC(B)} = 3.3\text{ V}$	-	1	-	pF
$C_{I/O}$	input/output capacitance	A port	-	5	-	pF
		B port	-	8.5	-	pF
		A or B port; $V_{CC(A)} = 3.3\text{ V}; V_{CC(B)} = 3.3\text{ V}$	-	11	-	pF

[1] V_{CCO} is the supply voltage associated with the output.

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	A port					
		$V_{CC(A)} = 1.65 \text{ V to } 1.95 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	[1] $V_{CCI} - 0.2$	-	$V_{CCI} - 0.2$	-	V
		$V_{CC(A)} = 2.3 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	[1] $V_{CCI} - 0.4$	-	$V_{CCI} - 0.4$	-	V
		B port					
		$V_{CC(A)} = 1.65 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	[1] $V_{CCI} - 0.4$	-	$V_{CCI} - 0.4$	-	V
V_{IL}	LOW-level input voltage	OE input					
		$V_{CC(A)} = 1.65 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	$0.65V_{CC(A)}$	-	$0.65V_{CC(A)}$	-	V
		A or B port					
V_{OH}	HIGH-level output voltage	$I_O = -20 \mu\text{A}$					
		$V_{CC(A)} = 1.65 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	[2] $0.67V_{CCO}$	-	$0.67V_{CCO}$	-	V
V_{OL}	LOW-level output voltage	A or B port; $I_O = 1 \text{ mA}$	[2]				
		$V_{CC(A)} = 1.65 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	-	0.4	-	0.4	V
I_I	input leakage current	OE input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 1.65 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	-	± 2	-	± 12	μA
I_{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO};$ $V_{CC(A)} = 1.65 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 2.3 \text{ V to } 5.5 \text{ V}$	[2]	± 2	-	± 12	μA
I_{OFF}	power-off leakage current	A port; $V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 0 \text{ V to } 5.5 \text{ V}$	-	± 2	-	± 12	μA
		B port; $V_I \text{ or } V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0 \text{ V}; V_{CC(A)} = 0 \text{ V to } 3.6 \text{ V}$	-	± 2	-	± 12	μA

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Max	Min	Max	
I_{CC}	supply current	$V_I = 0\text{ V}$ or V_{CCI} ; $I_O = 0\text{ A}$ [1]					
		$I_{CC(A)}$					
		$V_{CC(A)} = 1.65\text{ V}$ to 3.6 V ; $V_{CC(B)} = 2.3\text{ V}$ to 5.5 V	-	2.4	-	15	μA
		$V_{CC(A)} = 3.6\text{ V}$; $V_{CC(B)} = 0\text{ V}$	-	2.2	-	15	μA
		$V_{CC(A)} = 0\text{ V}$; $V_{CC(B)} = 5.5\text{ V}$	-	-1	-	-8	μA
		$I_{CC(B)}$					
		$V_{CC(A)} = 1.65\text{ V}$ to 3.6 V ; $V_{CC(B)} = 2.3\text{ V}$ to 5.5 V	-	12	-	30	μA
		$V_{CC(A)} = 3.6\text{ V}$; $V_{CC(B)} = 0\text{ V}$	-	-1	-	-5	μA
		$V_{CC(A)} = 0\text{ V}$; $V_{CC(B)} = 5.5\text{ V}$	-	1	-	6	μA
		$I_{CC(A)} + I_{CC(B)}$					
		$V_{CC(A)} = 1.65\text{ V}$ to 3.6 V ; $V_{CC(B)} = 2.3\text{ V}$ to 5.5 V	-	14.4	-	30	μA

[1] V_{CCI} is the supply voltage associated with the input.[2] V_{CCO} is the supply voltage associated with the output.

12. Dynamic characteristics

Table 9. Dynamic characteristics for temperature range –40 °C to +85 °C [\[1\]](#)Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}						Unit
			2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	
V _{CC(A)} = 1.8 V ± 0.15 V									
t _{PHL}	HIGH to LOW propagation delay	A to B	-	4.6	-	4.7	-	5.8	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	-	6.8	-	6.8	-	7.0	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	-	4.4	-	4.5	-	4.7	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	-	5.3	-	4.5	-	0.5	ns
t _{en}	enable time	OE to A; B	-	200	-	200	-	200	ns
t _{dis}	disable time	OE to A; no external load [2]	-	25	-	25	-	25	ns
		OE to B; no external load [2]	-	25	-	25	-	25	ns
		OE to A	-	230	-	230	-	230	ns
		OE to B	-	200	-	200	-	200	ns
t _{TLH}	LOW to HIGH output transition time	A port	3.2	9.5	2.3	9.3	1.8	7.6	ns
		B port	3.3	10.8	2.7	9.1	2.7	7.6	ns

Dual supply translating transceiver; open drain; auto direction sensing

Table 9. Dynamic characteristics for temperature range -40°C to $+85^{\circ}\text{C}$ ^[1]Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}						Unit	
			2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V			
			Min	Max	Min	Max	Min	Max		
t _{THL}	HIGH to LOW output transition time	A port	2.0	5.9	1.9	6.0	1.7	13.3	ns	
		B port	2.9	7.6	2.8	7.5	2.8	10.0	ns	
t _{sk(0)}	skew	between channels	[3]	-	0.7	-	0.7	-	0.7	ns
t _W	pulse width	data inputs		20	-	20	-	20	-	ns
f _{data}	data rate			-	50	-	50	-	50	Mbps
V _{CC(A)} = 2.5 V ± 0.2 V										
t _{PHL}	HIGH to LOW propagation delay	A to B		-	3.2	-	3.3	-	3.4	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		-	3.5	-	4.1	-	4.4	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		-	3.0	-	3.6	-	4.3	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		-	2.5	-	1.6	-	0.7	ns
t _{en}	enable time	OE to A; B		-	200	-	200	-	200	ns
t _{dis}	disable time	OE to A; no external load	[2]	-	20	-	20	-	20	ns
		OE to B; no external load	[2]	-	20	-	20	-	20	ns
		OE to A		-	200	-	200	-	200	ns
		OE to B		-	200	-	200	-	200	ns
t _{TLH}	LOW to HIGH output transition time	A port		2.8	7.4	2.6	6.6	1.8	6.2	ns
		B port		3.2	8.3	2.9	7.9	2.4	6.8	ns
t _{THL}	HIGH to LOW output transition time	A port		1.9	5.7	1.9	5.5	1.8	5.3	ns
		B port		2.2	7.8	2.4	6.7	2.6	6.6	ns
t _{sk(0)}	skew	between channels	[3]	-	0.7	-	0.7	-	0.7	ns
t _W	pulse width	data inputs		20	-	20	-	20	-	ns
f _{data}	data rate			-	50	-	50	-	50	Mbps
V _{CC(A)} = 3.3 V ± 0.3 V										
t _{PHL}	HIGH to LOW propagation delay	A to B		-	-	-	2.4	-	3.1	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		-	-	-	4.2	-	4.4	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		-	-	-	2.5	-	3.3	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		-	-	-	2.5	-	2.6	ns
t _{en}	enable time	OE to A; B		-	-	-	200	-	200	ns

Table 9. Dynamic characteristics for temperature range –40 °C to +85 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}						Unit
			2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	
t _{dis}	disable time	OE to A; no external load [2]	-	-	-	15	-	15	ns
		OE to B; no external load [2]	-	-	-	15	-	15	ns
		OE to A	-	-	-	260	-	260	ns
		OE to B	-	-	-	200	-	200	ns
t _{TLH}	LOW to HIGH output transition time	A port	-	-	2.3	5.6	1.9	5.9	ns
		B port	-	-	2.5	6.4	2.1	7.4	ns
t _{THL}	HIGH to LOW output transition time	A port	-	-	2.0	5.4	1.9	5.0	ns
		B port	-	-	2.3	7.4	2.4	7.6	ns
t _{sk(0)}	skew	between channels [3]	-	-	-	0.7	-	0.7	ns
t _W	pulse width	data inputs	-	-	20	-	20	-	ns
f _{data}	data rate		-	-	-	50	-	50	Mbps

[1] t_{en} is the same as t_{pZL} and t_{pZH}.

t_{dis} is the same as t_{pLZ} and t_{pHZ}.

[2] Delay between OE going LOW and when the outputs are actually disabled.

[3] Skew between any two outputs of the same package switching in the same direction.

Table 10. Dynamic characteristics for temperature range –40 °C to +125 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}						Unit
			2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	
V _{CC(A)} = 1.8 V ± 0.15 V									
t _{PHL}	HIGH to LOW propagation delay	A to B	-	5.8	-	5.9	-	7.3	ns
t _{PLH}	LOW to HIGH propagation delay	A to B	-	8.5	-	8.5	-	8.8	ns
t _{PHL}	HIGH to LOW propagation delay	B to A	-	5.5	-	5.7	-	5.9	ns
t _{PLH}	LOW to HIGH propagation delay	B to A	-	6.7	-	5.7	-	0.7	ns
t _{en}	enable time	OE to A; B	-	200	-	200	-	200	ns
t _{dis}	disable time	OE to A; no external load [2]	-	30	-	30	-	30	ns
		OE to B; no external load [2]	-	30	-	30	-	30	ns
		OE to A	-	250	-	250	-	250	ns
		OE to B	-	220	-	220	-	220	ns
t _{TLH}	LOW to HIGH output transition time	A port	3.2	11.9	2.3	11.7	1.8	9.5	ns
		B port	3.3	13.5	2.7	11.4	2.7	9.5	ns

Table 10. Dynamic characteristics for temperature range -40°C to $+125^{\circ}\text{C}$ [\[1\]](#) ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}						Unit	
			2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V			
			Min	Max	Min	Max	Min	Max		
t _{THL}	HIGH to LOW output transition time	A port	2.0	7.4	1.9	7.5	1.7	16.7	ns	
		B port	2.9	9.5	2.8	9.4	2.8	12.5	ns	
t _{sk(0)}	skew	between channels	[3]	-	0.8	-	0.8	-	0.8	ns
t _W	pulse width	data inputs		20	-	20	-	20	-	ns
f _{data}	data rate			-	50	-	50	-	50	Mbps
V _{CC(A)} = 2.5 V ± 0.2 V										
t _{PHL}	HIGH to LOW propagation delay	A to B		-	4.0	-	4.2	-	4.3	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		-	4.4	-	5.2	-	5.5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		-	3.8	-	4.5	-	5.4	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		-	3.2	-	2.0	-	0.9	ns
t _{en}	enable time	OE to A; B		-	200	-	200	-	200	ns
t _{dis}	disable time	OE to A; no external load	[2]	-	25	-	25	-	25	ns
		OE to B; no external load	[2]	-	25	-	25	-	25	ns
		OE to A		-	220	-	220	-	220	ns
		OE to B		-	220	-	220	-	220	ns
t _{TLH}	LOW to HIGH output transition time	A port		2.8	9.3	2.6	8.3	1.8	7.8	ns
		B port		3.2	10.4	2.9	9.7	2.4	8.3	ns
t _{THL}	HIGH to LOW output transition time	A port		1.9	7.2	1.9	6.9	1.8	6.7	ns
		B port		2.2	9.8	2.4	8.4	2.6	8.3	ns
t _{sk(0)}	skew	between channels	[3]	-	0.8	-	0.8	-	0.8	ns
t _W	pulse width	data inputs		20	-	20	-	20	-	ns
f _{data}	data rate			-	50	-	50	-	50	Mbps
V _{CC(A)} = 3.3 V ± 0.3 V										
t _{PHL}	HIGH to LOW propagation delay	A to B		-	-	-	3.0	-	3.9	ns
t _{PLH}	LOW to HIGH propagation delay	A to B		-	-	-	5.3	-	5.5	ns
t _{PHL}	HIGH to LOW propagation delay	B to A		-	-	-	3.2	-	4.2	ns
t _{PLH}	LOW to HIGH propagation delay	B to A		-	-	-	3.2	-	3.3	ns
t _{en}	enable time	OE to A; B		-	-	-	200	-	200	ns

Table 10. Dynamic characteristics for temperature range -40°C to $+125^{\circ}\text{C}$ [\[1\]](#) ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#); for wave forms see [Figure 5](#) and [Figure 6](#).

Symbol	Parameter	Conditions	V _{CC(B)}						Unit
			2.5 V ± 0.2 V		3.3 V ± 0.3 V		5.0 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	
t _{dis}	disable time	OE to A; no external load [2]	-	-	-	20	-	20	ns
		OE to B; no external load [2]	-	-	-	20	-	20	ns
		OE to A	-	-	-	280	-	280	ns
		OE to B	-	-	-	220	-	220	ns
t _{TLH}	LOW to HIGH output transition time	A port	-	-	2.3	7.0	1.9	7.4	ns
		B port	-	-	2.5	8.0	2.1	9.3	ns
t _{THL}	HIGH to LOW output transition time	A port	-	-	2.0	6.8	1.9	6.3	ns
		B port	-	-	2.3	9.3	2.4	9.5	ns
t _{sk(0)}	skew	between channels [3]	-	-	-	0.8	-	0.8	ns
t _W	pulse width	data inputs	-	-	20	-	20	-	ns
f _{data}	data rate		-	-	-	50	-	50	Mbps

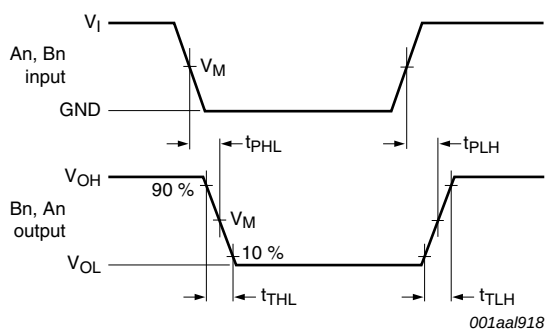
[1] t_{en} is the same as t_{PZL} and t_{PZH} .

t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[2] Delay between OE going LOW and when the outputs are actually disabled.

[3] Skew between any two outputs of the same package switching in the same direction.

13. Waveforms



Measurement points are given in [Table 11](#).

V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The data input (An, Bn) to data output (Bn, An) propagation delay times

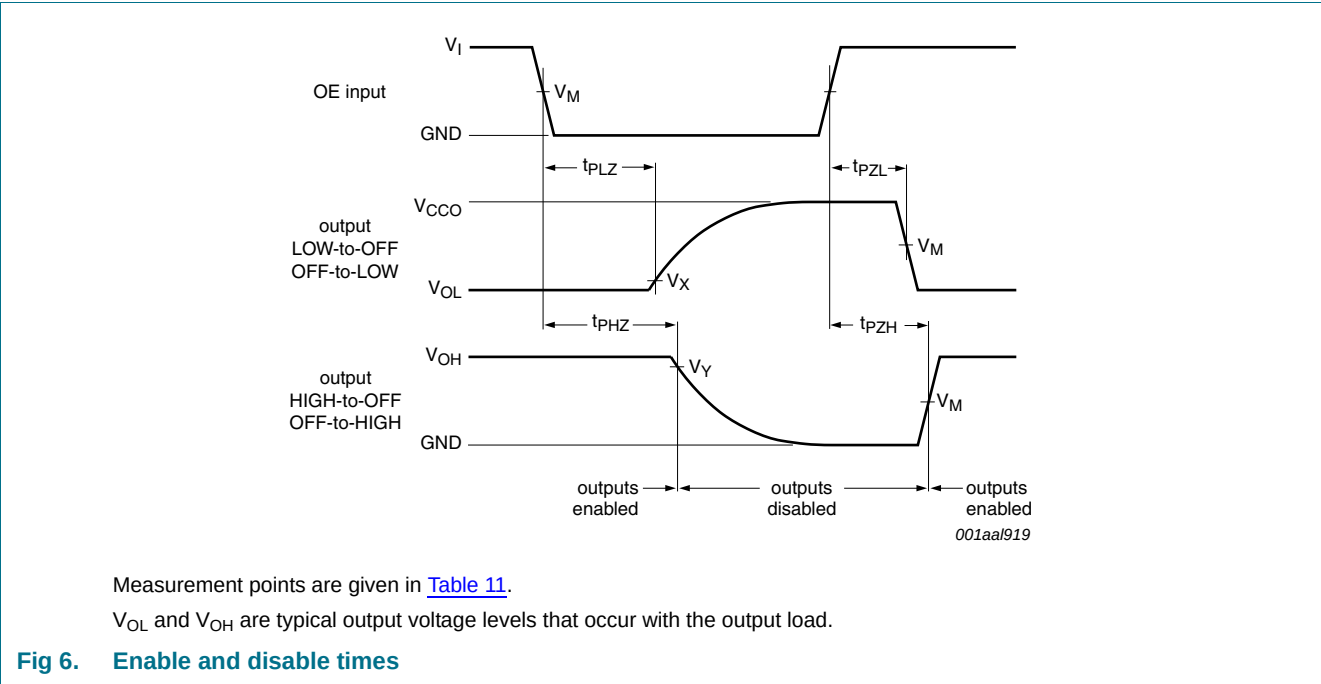


Table 11. Measurement points^{[1][2]}

Supply voltage	Input	Output		
V _{CCO}	V _M	V _M	V _X	V _Y
1.8 V ± 0.15 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
2.5 V ± 0.2 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V
3.3 V ± 0.3 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V
5.0 V ± 0.5 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V

[1] V_{CCI} is the supply voltage associated with the input.
[2] V_{CCO} is the supply voltage associated with the output.

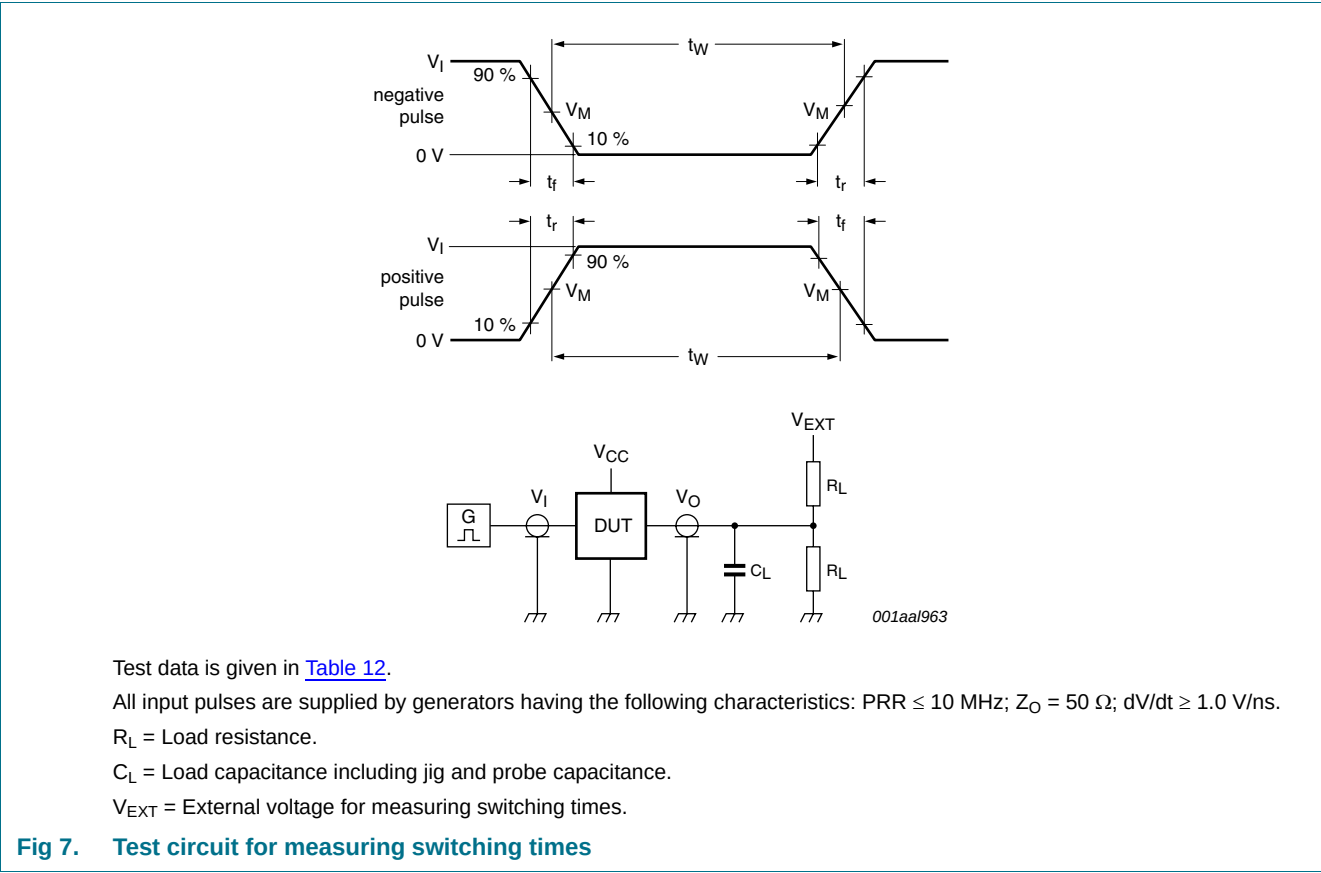


Table 12. Test data

Supply voltage		Input		Load		V _{EXT}		
V _{CC(A)}	V _{CC(B)}	V _I ^[1]	Δt/ΔV	C _L	R _L ^[2]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} ^[3]
1.65 V to 3.6 V	2.3 V to 5.5 V	V _{CCI}	≤ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V _{CCO}

- [1] V_{CCI} is the supply voltage associated with the input.
- [2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, R_L = 1 MΩ; for measuring enable and disable times, R_L = 50 KΩ.
- [3] V_{CCO} is the supply voltage associated with the output.

14. Application information

14.1 Applications

Voltage level-translation applications. The NXS0102 can be used in point-to-point applications to interface between devices or systems operating at different supply voltages. The device is primarily targeted at I²C or 1-wire which use open-drain drivers, it may also be used in applications where push-pull drivers are connected to the ports, however the NXB0102 may be more suitable.

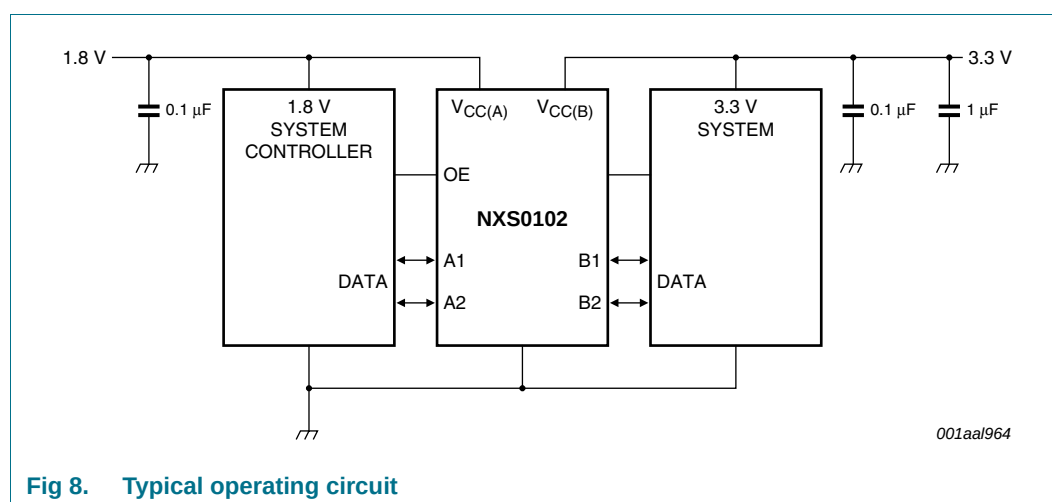


Fig 8. Typical operating circuit

14.2 Architecture

The architecture of the NXS0102 is shown in Figure 9. The device does not require an extra input signal to control the direction of data flow from A to B or B to A.

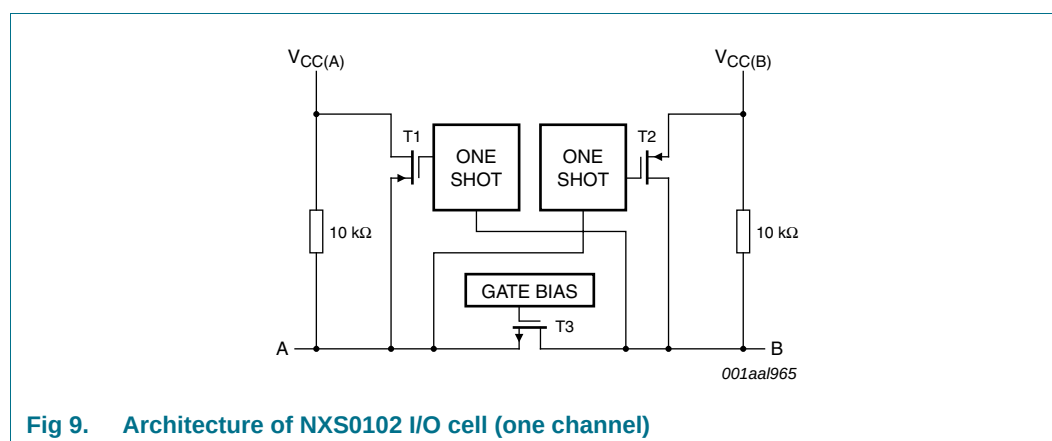


Fig 9. Architecture of NXS0102 I/O cell (one channel)

The NXS0102 is a "switch" type voltage translator, it employs two key circuits to enable voltage translation:

1. A pass-gate transistor (N-channel) that ties the ports together.
2. An output edge-rate accelerator that detects and accelerates rising edges on the I/O pins.

The gate bias voltage of the pass gate transistor (T3) is set at approximately one threshold voltage above the V_{CC} level of the low-voltage side. During a LOW-to-HIGH transition the output one-shot accelerates the output transition by switching on the PMOS transistors (T1, T2) bypassing the 10 k Ω pull-up resistors and increasing current drive capability. The one-shot is activated once the input transition reaches approximately $V_{CC}/2$; it is de-activated approximately 50 ns after the output reaches $V_{CCO}/2$. During the acceleration time the driver output resistance is between approximately 50 Ω and 70 Ω . To avoid signal contention and minimize dynamic I_{CC} , the user should wait for the one-shot circuit to turn-off before applying a signal in the opposite direction. Pull-up resistors are included in the device for DC current sourcing capability.

14.3 Input driver requirements

As the NXS0102 is a switch type translator, properties of the input driver directly effect the output signal. The external open-drain or push-pull driver applied to an I/O determines the static current sinking capability of the system; the max data rate, HIGH-to-LOW output transition time (t_{THL}) and propagation delay (t_{PHL}) are dependent upon the output impedance and edge-rate of the external driver. The limits provided for these parameters in the datasheet assume a driver with output impedance below 50 Ω is used.

14.4 Output load considerations

The maximum lumped capacitive load that can be driven is dependant upon the one-shot pulse duration. In cases with very heavy capacitive loading there is a risk that the output will not reach the positive rail within the one-shot pulse duration.

To avoid excessive capacitive loading and to ensure correct triggering of the one-shot it's recommended to use short trace lengths and low capacitance connectors on NXS0102 PCB layouts. To ensure low impedance termination and avoid output signal oscillations and one-shot re-triggering, the length of the PCB trace should be such that the round trip delay of any reflection is within the one-shot pulse duration (approximately 50 ns).

14.5 Power up

During operation $V_{CC(A)}$ must never be higher than $V_{CC(B)}$, however during power-up $V_{CC(A)} \geq V_{CC(B)}$ does not damage the device, so either power supply can be ramped up first. There is no special power-up sequencing required. The NXS0102 includes circuitry that disables all output ports when either $V_{CC(A)}$ or $V_{CC(B)}$ is switched off.

14.6 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW

causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND through a pull-down resistor, the minimum value of the resistor is determined by the current-sourcing capability of the driver.

14.7 Pull-up or pull-down resistors on I/Os lines

Each A port I/O has an internal 10 k Ω pull-up resistor to $V_{CC(A)}$, and each B port I/O has an internal 10 k Ω pull-up resistor to $V_{CC(B)}$. If a smaller value of pull-up resistor is required, an external resistor must be added parallel to the internal 10 k Ω , this will effect the V_{OL} level. When OE goes LOW the internal pull-ups of the NXS0102 are disabled.

15. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

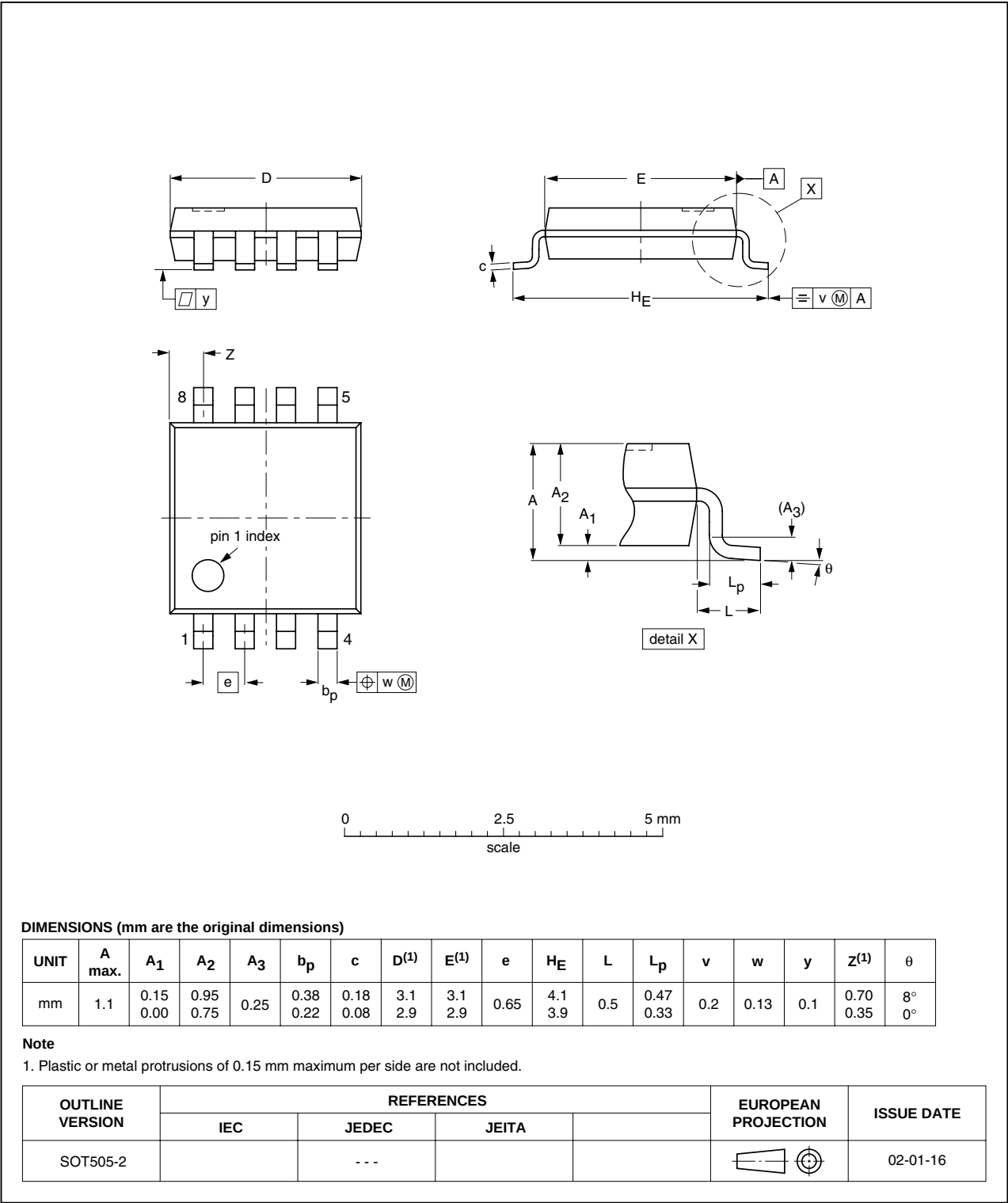


Fig 10. Package outline SOT505-2 (TSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

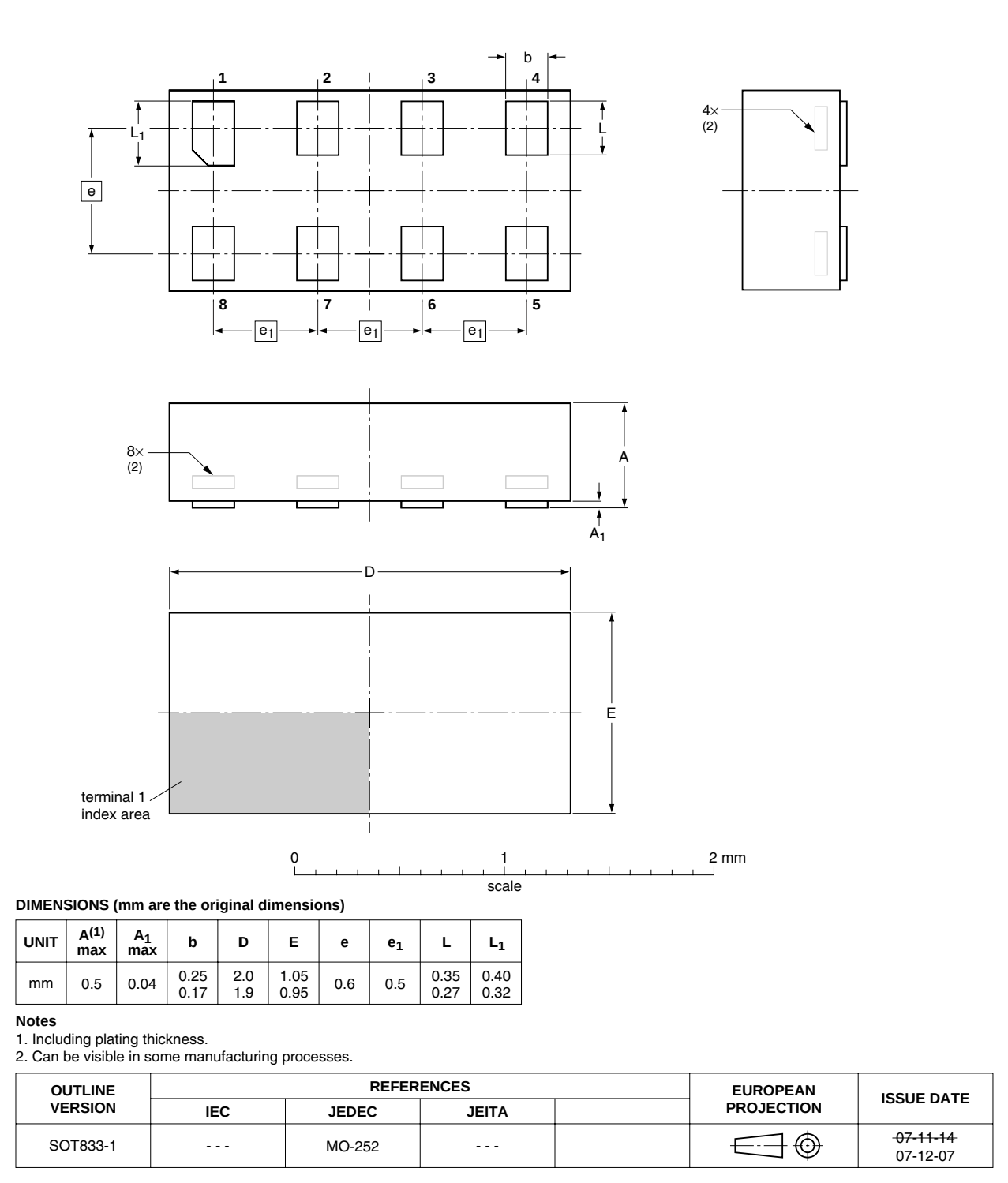


Fig 11. Package outline SOT833-1 (XSON8)

XSON8U: plastic extremely thin small outline package; no leads;
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

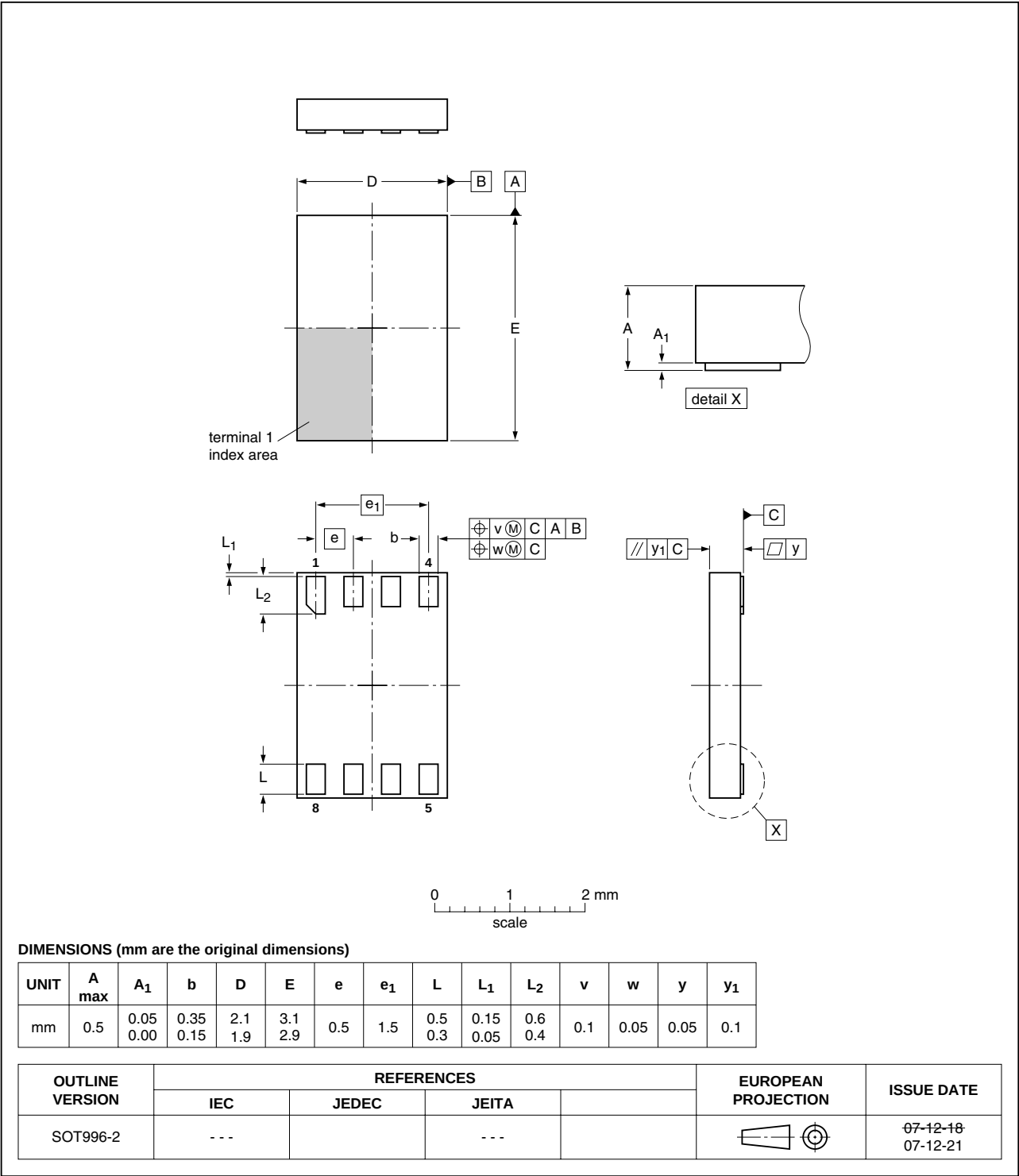


Fig 12. Package outline SOT996-2 (XSON8U)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1 x 0.5 mm

SOT1089

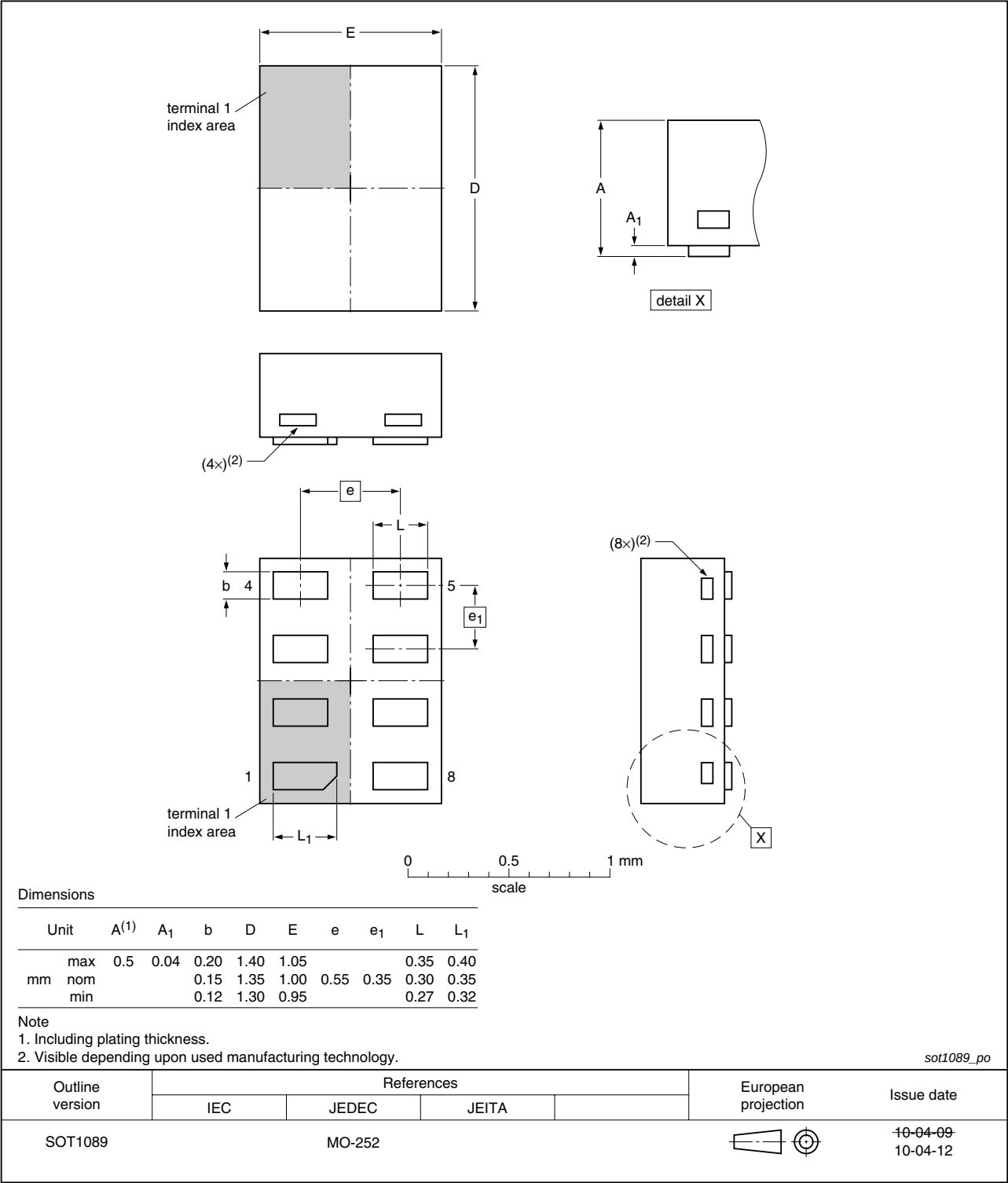


Fig 13. Package outline SOT1089 (XSON8)

16. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
GPIO	General Purpose Input Output
HBM	Human Body Model
I ² C	Inter-Integrated Circuit
MM	Machine Model
PCB	Printed Circuit Board
PMOS	Positive Metal Oxide Semiconductor
SMBus	System Management Bus
UART	Universal Asynchronous Receiver Transmitter
UTLP	Ultra Thin Leadless Package

17. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NXS0102_1	20100602	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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20. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Ordering information	2
5	Marking	2
6	Functional diagram	2
7	Pinning information	3
7.1	Pinning	3
7.2	Pin description	3
8	Functional description	4
9	Limiting values	4
10	Recommended operating conditions	5
11	Static characteristics	5
12	Dynamic characteristics	7
13	Waveforms	11
14	Application information	14
14.1	Applications	14
14.2	Architecture	14
14.3	Input driver requirements	15
14.4	Output load considerations	15
14.5	Power up	15
14.6	Enable and disable	15
14.7	Pull-up or pull-down resistors on I/Os lines . .	16
15	Package outline	17
16	Abbreviations	21
17	Revision history	21
18	Legal information	22
18.1	Data sheet status	22
18.2	Definitions	22
18.3	Disclaimers	22
18.4	Trademarks	23
19	Contact information	23
20	Contents	24

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